National Semiconductor

54F/74F676 16-Bit Serial/Parallel-In, Serial-Out Shift Register

General Description

The 'F676 contains 16 flip-flops with provision for synchronous parallel or serial entry and serial output. When the Mode (M) input is HIGH, information present on the parallel data (P₀-P₁₅) inputs is entered on the falling edge of the Clock Pulse (CP) input signal. When M is LOW, data is shifted out of the most significant bit position while information present on the Serial (SI) input shifts into the least significant bit position. A HIGH signal on the Chip Select (CS) input prevents both parallel and serial operations.

Features

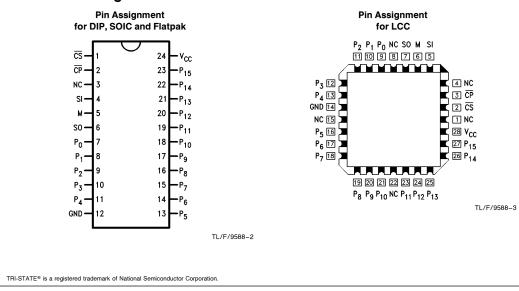
- 16-bit parallel-to-serial conversion
- 16-bit serial-in, serial-out
- Chip select control
- Slim 24 lead 300 mil package

Commercial	Military	Package Number	Package Description
74F676PC		N24A	24-Lead (0.600" Wide) Molded Dual-In-Line
74F676SPC		N24C	24-Lead (0.300" Wide) Molded Dual-In-Line
	54F676DM (Note 2)	J24A	24-Lead (0.600" Wide) Ceramic Dual-In-Line
	54F676SDM (Note 2)	J24F	24-Lead (0.300" Wide) Ceramic Dual-In-Line
74F676SC (Note 1)		M24B	24-Lead (0.300" Wide) Molded Small Outline, JEDEC
	54F676FM (Note 2)	W24C	24-Lead Cerpack
	54F676LM (Note 2)	E28A	24-Lead Ceramic Leadless Chip Carrier, Type C

Note 1: Devices also available in 13" reel. Use suffix = SCX.

Note 2: Military grade device with environmental and burn-in processing. Use suffix = DMQB, FMQB and LMQB.

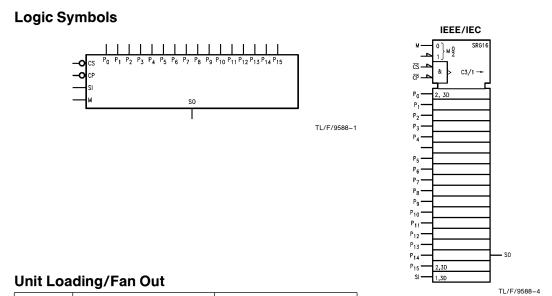
Connection Diagrams



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		54	F/74F
Pin Names	Description	U.L. HIGH/LOW	Input I _{IH} /I _{IL} Output I _{OH} /I _{OL}
$\frac{P_0 - P_{15}}{CS}$	Parallel Data Inputs	1.0/1.0	$20 \ \mu A / -0.6 \ m A$
	Chip Select Input (Active LOW)	1.0/1.0	20 μ A/-0.6 mA
CP	Clock Pulse Input (Active LOW)	1.0/1.0	20 µA/−0.6 mA
M	Mode Select Input	1.0/1.0	20 µA/−0.6 mA
SI	Serial Data Input	1.0/1.0	20 µA/−0.6 mA
SO	Serial Output	50/33.3	-1 mA/20 mA

Functional Description

The 16-bit shift register operates in one of three modes, as indicated in the Shift Register Operations Table.

HOLD-a HIGH signal on the Chip Select (CS) input prevents clocking, and data is stored in the sixteen registers.

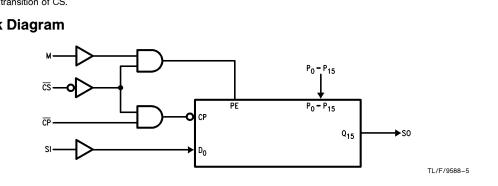
Shift/Serial Load—data present on the SI pin shifts into the register on the falling edge of \overline{CP} . Data enters the Q_0 position and shifts toward Q15 on successive clocks, finally appearing on the SO pin.

Parallel Load—data present on P_0-P_{15} are entered into the register on the falling edge of \overline{CP} . The SO output represents the Q₁₅ register output.

To prevent false clocking, \overline{CP} must be LOW during a LOW-to-HIGH transition of $\overline{CS}.$

Block Diagram

Shift Register Operations Table **Control Input Operating Mode** CS CP М н Hold Х Х L L Shift/Serial Load Parallel Load L н H = HIGH Voltage Level L = LOW Voltage Level X = Immaterial $\sim = HIGH-to-LOW Transition$



Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature	-65°C to +150°C
Ambient Temperature under Bias	-55°C to +125°C
Junction Temperature under Bias Plastic	−55°C to +175°C −55°C to +150°C
V _{CC} Pin Potential to Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to $+7.0V$
Input Current (Note 2)	-30 mA to $+5.0$ mA
Voltage Applied to Output in HIGH State (with $V_{CC} = 0V$)	
Standard Output	-0.5V to V _{CC}
TRI-STATE [®] Output	-0.5V to $+5.5V$
Current Applied to Output	

in LOW State (Max) twice the rated I_{OL} (mA) Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

DC Electrical Characteristics

Recommended Operating Conditions

Free Air Ambient Temperature

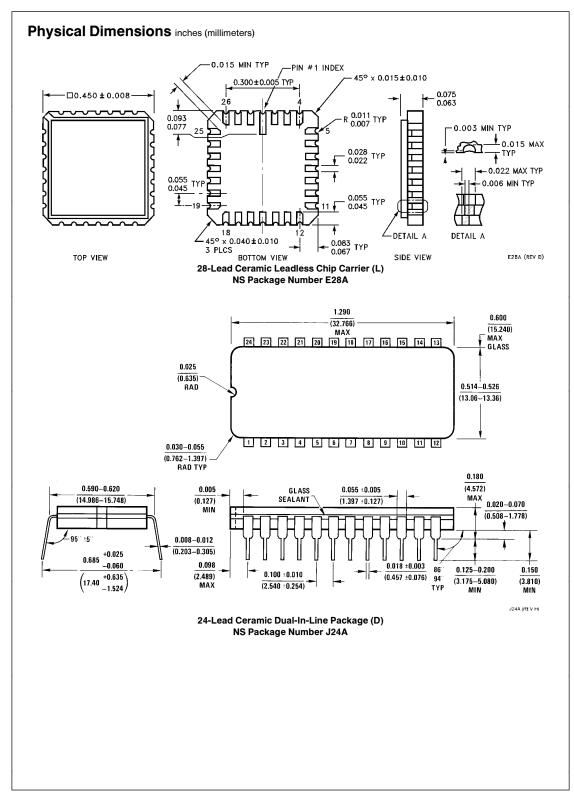
Symbol	Parameter			54F/74F			Vcc	Conditions
	Faiane		Min	Тур	Max	Units	VCC	Conditions
VIH	Input HIGH Voltage		2.0			V		Recognized as a HIGH Sign
VIL	Input LOW Voltage				0.8	V		Recognized as a LOW Signa
V _{CD}	Input Clamp Diode Vo	oltage			-1.2	V	Min	$I_{IN} = -18 \text{ mA}$
V _{OH}	Output HIGH Voltage	54F 10% V _{CC} 74F 10% V _{CC} 74F 5% V _{CC}	2.5 2.5 2.7			V	Min	$I_{OH} = -1 \text{ mA}$ $I_{OH} = -1 \text{ mA}$ $I_{OH} = -1 \text{ mA}$
V _{OL}	Output LOW Voltage	54F 10% V _{CC} 74F 10% V _{CC}			0.5 0.5	V	Min	$I_{OL} = 20 \text{ mA}$ $I_{OL} = 20 \text{ mA}$
IIH	Input HIGH Current	54F 74F			20.0 5.0	μΑ	Max	$V_{IN} = 2.7V$
I _{BVI}	Input HIGH Current Breakdown Test	54F 74F			100 7.0	μΑ	Max	$V_{IN} = 7.0V$
ICEX	Output HIGH Leakage Current	54F 74F			250 50	μΑ	Max	$V_{OUT} = V_{CC}$
V _{ID}	Input Leakage Test	74F	4.75			V	0.0	$I_{ID} = 1.9 \ \mu A$, All Other Pins Grounded
I _{OD}	Output Leakage Circuit Current	74F			3.75	μΑ	0.0	V _{IOD} = 150 mV, All Other Pins Grounded
IIL	Input LOW Current				-0.6	mA	Max	$V_{IN} = 0.5V$
I _{OS}	Output Short-Circuit (Current	-60		-150	mA	Мах	$V_{OUT} = 0V$
ICC	Power Supply Curren	t			72	mA	Max	

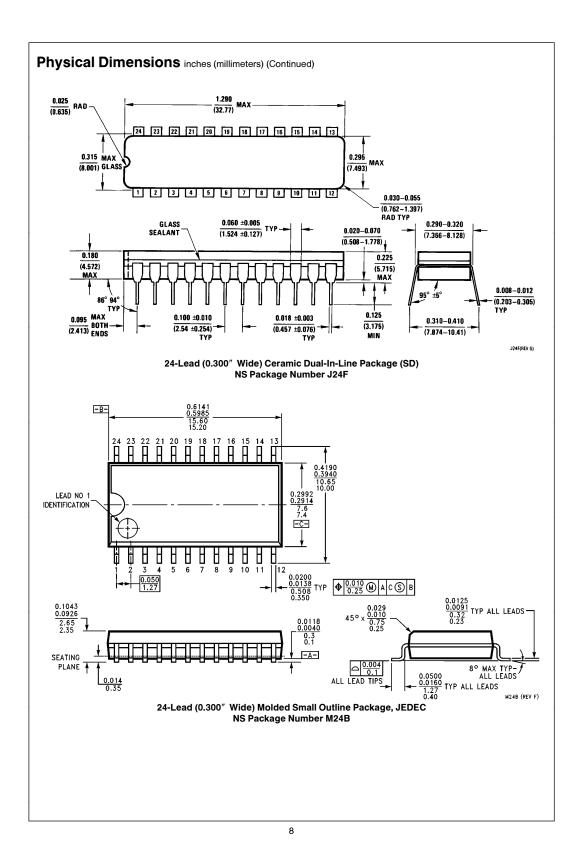
AC EI	ectrical Characteri	stics							
			74F		5	4F	7	4F	
Symbol	Parameter	$\label{eq:transform} \begin{array}{ c c c } T_A = +25^\circ C & & & \\ V_{CC} = +5.0V & & & \\ C_L = 50 \ pF & & & \\ \end{array} \begin{array}{ c c } T_A, \ V_{CC} = Mil \\ C_L = 50 \ pF \end{array}$						Units	
		Min	Тур	Мах	Min	Мах	Min	Мах	
f _{max}	Maximum Clock Frequency	100	110		45		90		MHz
t _{PLH} t _{PHL}	Propagation Delay \overline{CP} to SO	4.5 5.0	9.0 9.0	11.0 12.5	4.5 5.0	17.0 14.5	4.5 5.0	12.0 13.5	ns

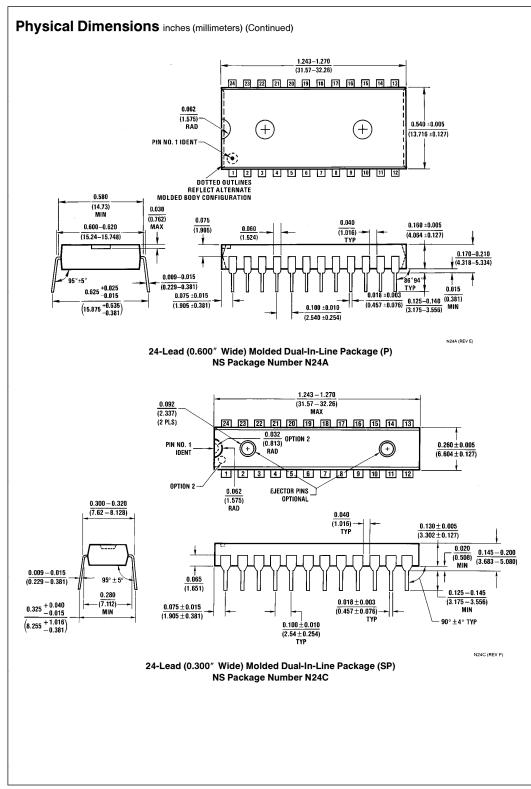
AC Operating Requirements

		7	4F	54	54F74FT_A, V_{CC} = MilT_A, V_{CC} = Com		4F	
Symbol	Parameter		+ 25°C + 5.0V	T _A , V _{CC}			m Units	
		Min	Max	Min	Max	Min	Max	
t _s (H) t _s (L)	Setup Time, HIGH or LOW SI to CP	4.0 4.0		4.0 4.0		4.0 4.0		
t _h (H) t _h (L)	Hold Time, HIGH or LOW SI to CP	4.0 4.0		4.0 4.0		4.0 4.0		– ns
t _s (H) t _s (L)	Setup Time, HIGH or LOW P _n to CP	3.0 3.0		3.0 3.0		3.0 3.0		- ns
t _h (H) t _h (L)	Hold Time, HIGH or LOW P _n to CP	4.0 4.0		4.0 4.0		4.0 4.0		
t _s (H) t _s (L)	Setup Time, HIGH or LOW M to \overline{CP}	8.0 8.0		8.0 8.0		8.0 8.0		ns
t _h (H) t _h (L)	Hold Time, HIGH or LOW M to CP	2.0 2.0		2.0 2.0		2.0 2.0		113
t _s (L)	Setup Time, LOW CS to CP	10.0		12.0		10.0		20
t _h (H)	Hold Time, HIGH CS to CP	10.0		10.0		10.0		- ns
t _w (H) t _w (L)	CP Pulse Width HIGH or LOW	4.0 6.0		5.0 9.0		4.0 6.0		ns

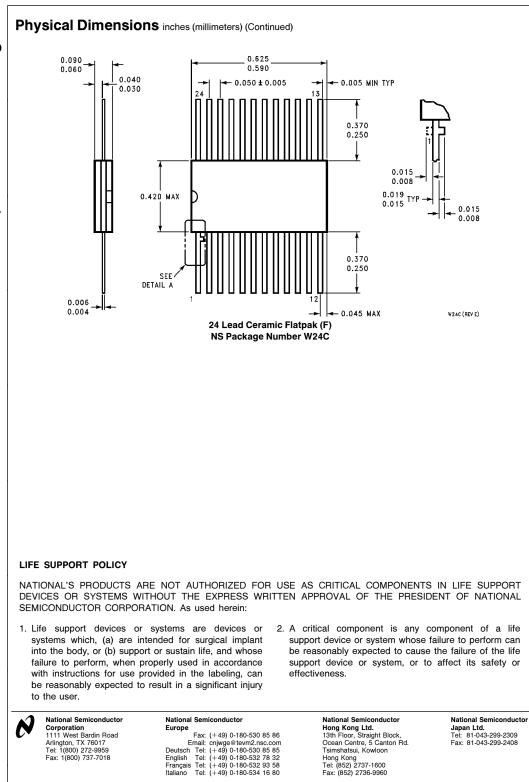
Temperature Range Family 74F = Commercial 54F = Military	<u>74F</u>	676	<u>s</u> (Special Variations QB = Military grade device with environmental and burn-in
Device Type				processing
Package Code P = Plastic DIP SP = Slim Plastic DIP D = Ceramic DIP SD = Slim Ceramic DIP F = Flatpak L = Leadless Chip Carrier (LCC) S = Small Outline SOIC JEDEC				- Temperature Range C=Commercial (0°C to +70°C) M=Military (-55°C to +125°C)











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